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RLT1060-50G TECHNICAL DATA



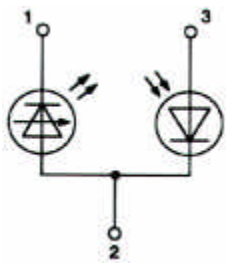
High Power Infrared Laserdiode

Structure: **QW structure**
Lasing wavelength: **1060 nm typ.**
Lasing Aperture: **1.5 x 3 μm^2**
Max. optical power: **50 mW, single mode**
Package: **9 mm**

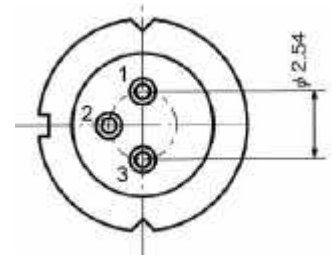
NOTE!
LASERDIODE
MUST BE COOLED!



PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	55	mW
LD Reverse Voltage	$V_{R(LD)}$	1.5	V
PD Reverse Voltage	$V_{R(PD)}$	6	V
Operating Temperature	T_c	-40 .. +60	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I_{th}	cw	15	20	35	mA
Operation Current	I_{op}	$P_o = 50 \text{ mW}$		120	200	mA
Forward Voltage	U_f	$P_o = 50 \text{ mW}$		1.8		V
Lasing Wavelength	λ_p	$P_o = 50 \text{ mW}$	1050	1060	1070	nm
Spectral Width (FWHM)	$\Delta\lambda$	$P_o = 50 \text{ mW}$		1.0	2.0	nm
Beam Divergence	$\theta_{//}$	$P_o = 50 \text{ mW}$		10		°
Beam Divergence	$\theta_{\perp}$	$P_o = 50 \text{ mW}$		40		°
Differential Efficiency	dP_o/dI_{op}	$P_o = 50 \text{ mW}$		0.2		mW/mA
Monitor Current	I_m	$P_o = 50 \text{ mW}$		300	750	μA